

**MSCSM120AM16CT1AG**  
**Datasheet**  
**Phase Leg MOSFET SiC Power Module**

January 2020



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a  **MICROCHIP** company

# Contents

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<b>1 Revision History.....</b>	<b>1</b>
Revision 1.0.....	1
<b>Product Overview.....</b>	<b>2</b>
2.1 Features.....	3
2.2 Benefits.....	3
2.3 Applications.....	3
<b>Electrical Specifications.....</b>	<b>4</b>
3.1 SiC MOSFET Characteristics (Per MOSFET).....	4
3.2 SiC Schottky Diode Ratings Characteristics (Per SiC Diode).....	6
3.3 Thermal Package Characteristics.....	6
3.4 Typical SiC MOSFET Performance Curves.....	8
3.5 Typical SiC Diode Performance Curves.....	11
<b>Package Specifications.....</b>	<b>12</b>

# Tables

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Table 1 • Absolute Maximum Ratings.....	4
Table 2 • Electrical Characteristics.....	4
Table 3 • Dynamic Characteristics.....	5
Table 4 • Body Diode Ratings and Characteristics.....	5
Table 5 • SiC Schottky Diode Ratings and Characteristics.....	6
Table 6 • Package Characteristics.....	6
Table 7 • Temperature Sensor NTC1.....	7

# Figures

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Figure 1 • MSCSM120AM16CT1AG Electrical Schematic.....	2
Figure 2 • MSCSM120AM16CT1AG Pinout Location.....	2
Figure 3 • Maximum Thermal Impedance.....	8
Figure 4 • Output Characteristics, T <sub>J</sub> = 25 °C.....	8
Figure 5 • Output Characteristics, T <sub>J</sub> = 175 °C.....	8
Figure 6 • Normalized RDS(on) vs. Temperature.....	8
Figure 7 • Transfer Characteristics.....	8
Figure 8 • Switching Energy vs. R <sub>g</sub> .....	9
Figure 9 • Switching Energy vs. Current.....	9
Figure 10 • Capacitance vs. Drain Source Voltage.....	9
Figure 11 • Gate Charge vs. Gate Source Voltage.....	9
Figure 12 • Body Diode Characteristics, T <sub>J</sub> = 25 °C.....	9
Figure 13 • 3rd Quadrant Characteristics, T <sub>J</sub> = 25 °C.....	9
Figure 14 • Body Diode Characteristics, T <sub>J</sub> = 175 °C.....	10
Figure 15 • 3rd Quadrant Characteristics, T <sub>J</sub> = 175 °C.....	10
Figure 16 • Operating Frequency vs. Drain Current.....	10
Figure 17 • Maximum Thermal Impedance.....	11
Figure 18 • Forward Characteristics.....	11
Figure 19 • Capacitance vs. Reverse Voltage.....	11
Figure 20 • Package Outline.....	12

# 1 Revision History

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The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

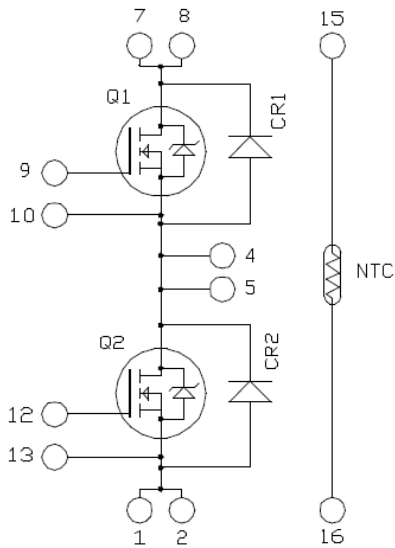
## 1.1 Revision 1.0

Revision 1.0 is the first publication of this document, published in January 2020.

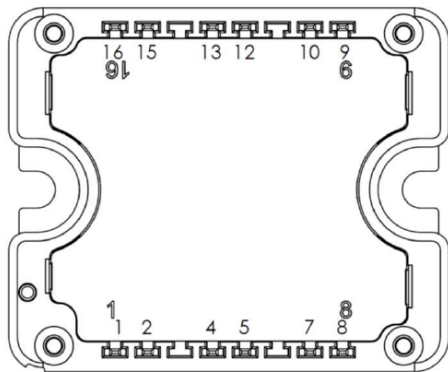
## 2 Product Overview

The MSCSM120AM16CT1AG is a phase leg 1200 V/173 A Silicon Carbide power module.

**Figure 1 • MSCSM120AM16CT1AG Electrical Schematic**



**Figure 2 • MSCSM120AM16CT1AG Pinout Location**



Pins 1/2 ; 4/5 ; 7/8 must be shorted together

All ratings at  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

**Caution:** These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

## 2.1 Features

The following are key features of the MSCSM120AM16CT1AG device:

- SiC Power MOSFET
  - Low RDS(on)
  - High temperature performance
- Silicon carbide (SiC) Schottky diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- Very low stray inductance
- Internal thermistor for temperature monitoring
- Aluminum nitride (AlN) substrate for improved thermal performance

## 2.2 Benefits

The following are benefits of the MSCSM120AM16CT1AG device:

- High power and high efficiency converters and inverters
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

## 2.3 Applications

The MSCSM120AM16CT1AG device is designed for the following applications:

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- EV motor and traction drive

## 3 Electrical Specifications

This section shows the electrical specifications of the MSCSM120AM16CT1AG device.

### 3.1 SiC MOSFET Characteristics (Per MOSFET)

This section describes the electrical characteristics of the MSCSM120AM16CT1AG device.

**Table 1 • Absolute Maximum Ratings**

Symbol	Parameter	Maximum Ratings	Unit
$V_{DSS}$	Drain-source voltage	1200	V
$I_D$	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	173 <sup>1</sup>
		$T_C = 80\text{ }^\circ\text{C}$	138 <sup>1</sup>
$I_{DM}$	Pulsed drain current	350	
$V_{GS}$	Gate-source voltage	-10/25	V
$R_{Dson}$	Drain-source ON resistance	16	m $\Omega$
$P_D$	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	745

**Note:**

1. Specification of SiC MOSFET device but output current must be limited due to the size of power connectors.

**Table 2 • Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}; V_{DS} = 1200\text{ V}$		20	200	$\mu\text{A}$
$R_{Dson}$	Drain-source on resistance	$V_{GS} = 20\text{ V}$ $I_D = 80\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	12.5	16	m $\Omega$
			$T_J = 175\text{ }^\circ\text{C}$	20		
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}, I_D = 2\text{ mA}$	1.8	2.8		V
$I_{GSS}$	Gate-source leakage current	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			200	nA



**Table 3 • Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}$ $V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$		6040		pF
$C_{oss}$	Output capacitance			540		
$C_{rss}$	Reverse transfer capacitance			50		
$Q_g$	Total gate charge	$V_{GS} = -5/20\text{ V}$ $V_{Bus} = 800\text{ V}$ $I_D = 80\text{ A}$		464		nC
$Q_{gs}$	Gate–source charge			82		
$Q_{gd}$	Gate–drain charge			100		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5/20\text{ V}$ $V_{Bus} = 600\text{ V}$ $I_D = 100\text{ A}$ $R_{Gon} = 4\Omega$ ; $R_{Goff} = 2.4\Omega$		30		ns
$T_r$	Rise time			30		
$T_{d(off)}$	Turn-off delay time			50		
$T_f$	Fall time			25		
$E_{on}$	Turn on energy	Inductive Switching $V_{GS} = -5/20\text{ V}$ $V_{Bus} = 600\text{ V}$ $I_D = 100\text{ A}$ $R_{Gon} = 4\Omega$ $R_{Goff} = 2.4\Omega$	$T_J = 150\text{ }^\circ\text{C}$	1.98		mJ
$E_{off}$	Turn off energy		$T_J = 150\text{ }^\circ\text{C}$	1.3		mJ
$R_{Gint}$	Internal gate resistance			2.94		$\Omega$
$R_{thJC}$	Junction-to-case thermal resistance				0.2	$^\circ\text{C/W}$

**Table 4 • Body Diode Ratings and Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{SD}$	Diode forward voltage	$V_{GS} = 0\text{ V}$ ; $I_{SD} = 80\text{ A}$		4		V
		$V_{GS} = -5\text{ V}$ ; $I_{SD} = 80\text{ A}$		4.2		
$t_{rr}$	Reverse recovery time	$I_{SD} = 80\text{ A}$ ; $V_{GS} = -5\text{ V}$ ; $V_R = 800\text{ V}$ ; $diF/dt = 2000\text{ A}/\mu\text{s}$		90		ns
$Q_{rr}$	Reverse recovery charge			1100		nC
$I_{rr}$	Reverse recovery current				27	

### 3.2 SiC Schottky Diode Ratings Characteristics (Per SiC Diode)

This section shows the SiC Schottky diode ratings and characteristics of the device.

**Table 5 • SiC Schottky Diode Ratings and Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Peak repetitive reverse voltage					1200	V
$I_{RRM}$	Reverse leakage current	$V_R = 1200\text{ V}$	$T_J = 25\text{ °C}$		20	400	$\mu\text{A}$
			$T_J = 175\text{ °C}$		300		
$I_F$	Forward current				60		A
$V_F$	Diode forward voltage	$I_F = 60\text{ A}$	$T_J = 25\text{ °C}$		1.5	1.8	V
			$T_J = 175\text{ °C}$		2.1		
$Q_C$	Total capacitive charge	$V_R = 600\text{ V}$			260		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$			282		pF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$			210		
$R_{thJC}$	Junction-to-case thermal resistance					0.477	$^{\circ}\text{C/W}$

### 3.3 Thermal Package Characteristics

This section shows the thermal and package characteristics of the device.

**Table 6 • Package Characteristics**

Symbol	Characteristic		Min	Max	Unit	
$V_{ISOL}$	RMS isolation voltage, any terminal to case $t = 1\text{ min}, 50/60\text{Hz}$		4000		V	
$T_J$	Operating junction temperature range		-40	175	$^{\circ}\text{C}$	
$T_{JOP}$	Recommended junction temperature under switching conditions		-40	$T_{Jmax} - 25$	$^{\circ}\text{C}$	
$T_{STG}$	Storage temperature range		-40	125	$^{\circ}\text{C}$	
$T_C$	Operating case temperature		-40	125	$^{\circ}\text{C}$	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight			80		g

**Table 7 • Temperature Sensor NTC<sup>1</sup>**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance at 25 °C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B		T <sub>C</sub> = 100 °C	4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

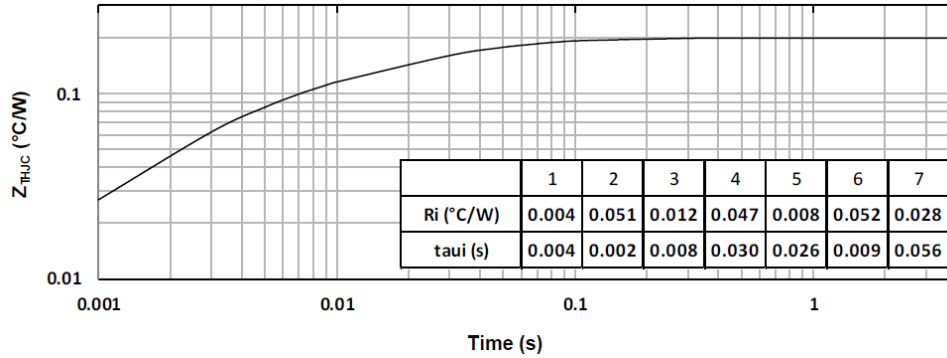
**Note:**

1. See application note APT0406 on [www.microsemi.com](http://www.microsemi.com).

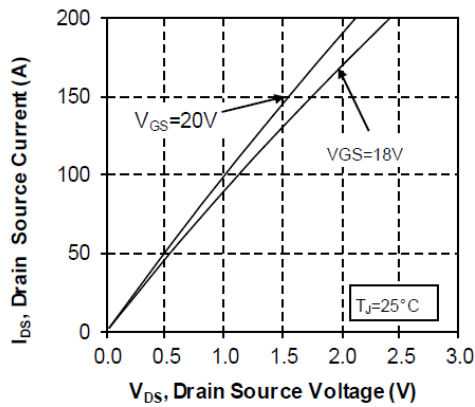
### 3.4 Typical SiC MOSFET Performance Curves

This section shows the typical performance curves of the MSCSM120AM016CT1AG SiC MOSFET.

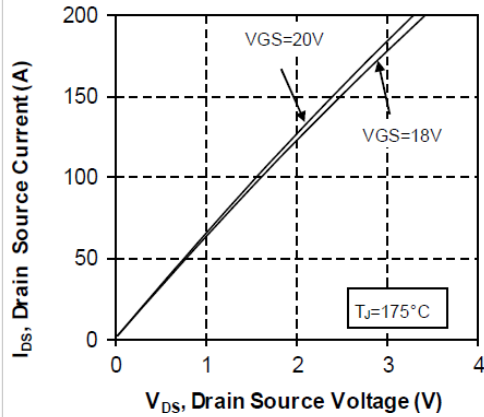
**Figure 3 • Maximum Thermal Impedance**



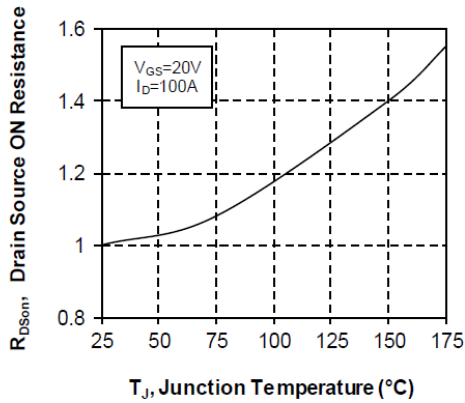
**Figure 4 • Output Characteristics, T<sub>J</sub> = 25 °C**



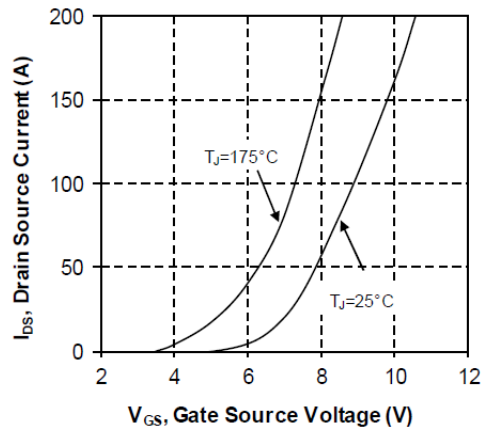
**Figure 5 • Output Characteristics, T<sub>J</sub> = 175 °C**



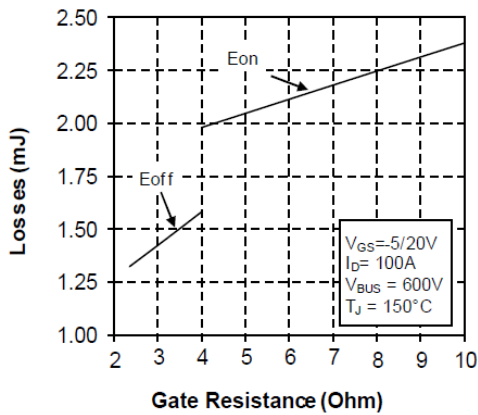
**Figure 6 • Normalized RDS(on) vs. Temperature**



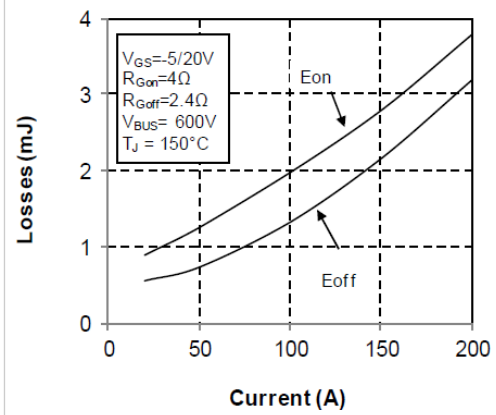
**Figure 7 • Transfer Characteristics**



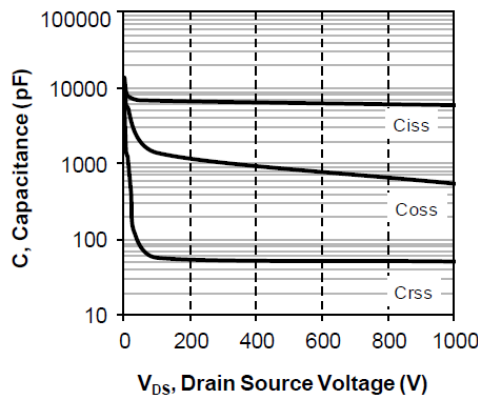
**Figure 8 • Switching Energy vs. Rg**



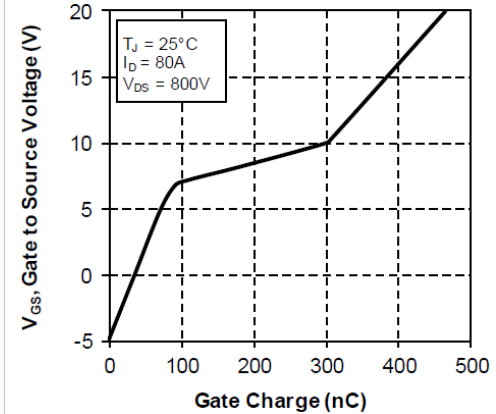
**Figure 9 • Switching Energy vs. Current**



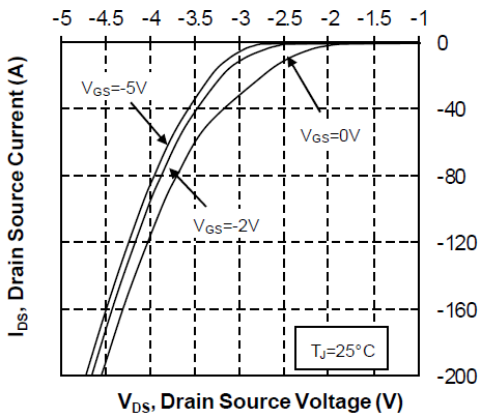
**Figure 10 • Capacitance vs. Drain Source Voltage**



**Figure 11 • Gate Charge vs. Gate Source Voltage**



**Figure 12 • Body Diode Characteristics, TJ = 25 °C**



**Figure 13 • 3<sup>rd</sup> Quadrant Characteristics, TJ = 25 °C**

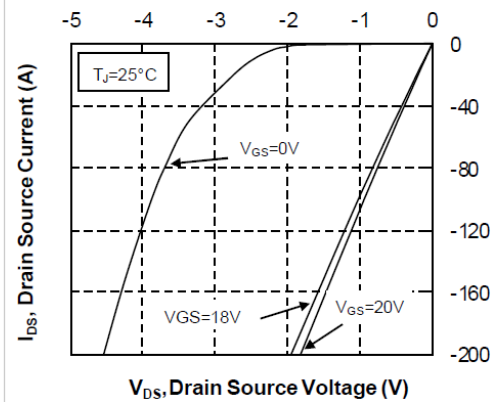


Figure 14 • Body Diode Characteristics,  $T_J = 175^\circ\text{C}$

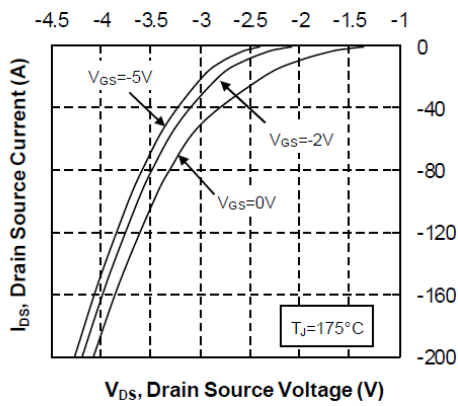


Figure 15 • 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 175^\circ\text{C}$

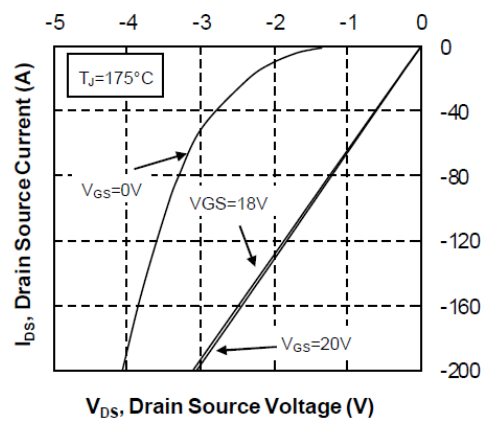
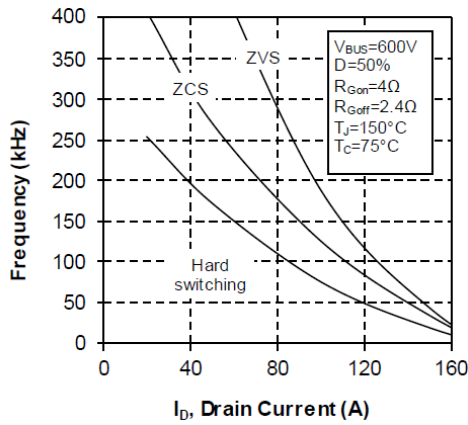


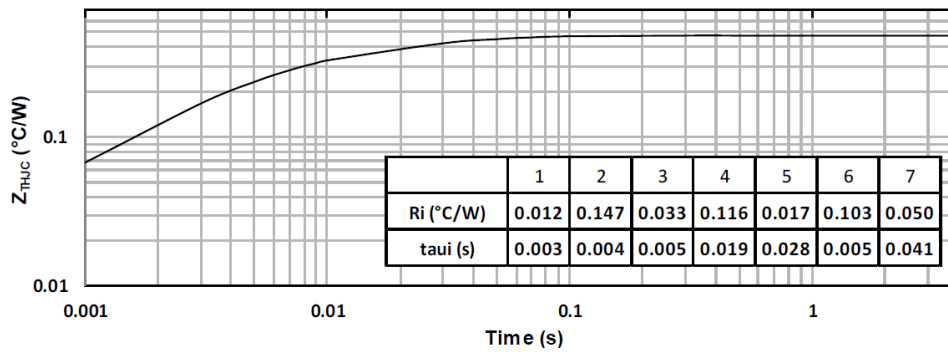
Figure 16 • Operating Frequency vs. Drain Current



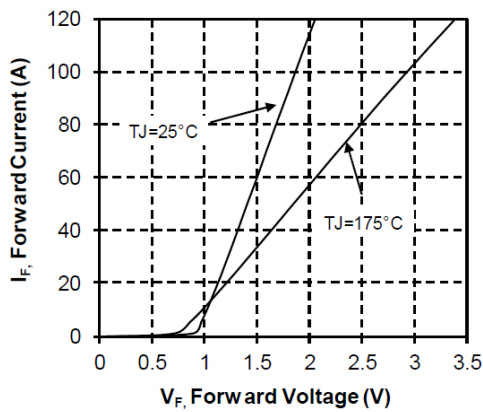
### 3.5 Typical SiC Diode Performance Curves

This section shows the typical performance curves of the MSCSM120AM16CT1AG SiC diode.

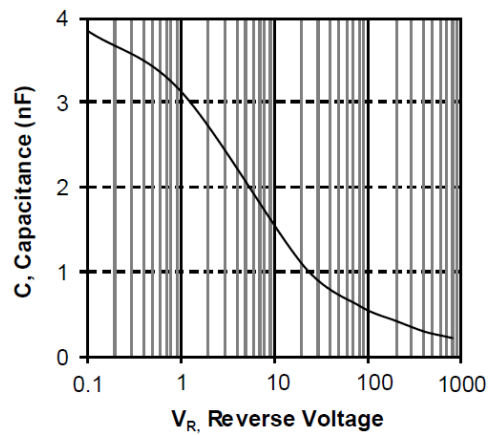
**Figure 17 • Maximum Thermal Impedance**



**Figure 18 • Forward Characteristics**



**Figure 19 • Capacitance vs. Reverse Voltage**







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